HITACHI

2SC5137

Silicon NPN Epitaxial Transistor

Application

VHF & UHF wide band amplifier

Features

- High gain bandwidth product
  f_T = 10 GHz typ.
- High gain, low noise figure
  PG = 16.5 dB typ.,
  NF = 1.5 dB typ. at f = 900 MHz

SMPAK

1. Emitter
2. Base
3. Collector

Table 1 Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	15	V
Collector to emitter voltage	V_{CEO}	8	V
Emitter to base voltage	V_{EBO}	1.5	V
Collector current	I_C	20	mA
Collector power dissipation	P_C	80	mW
Junction temperature	T_j	150	°C
Storage temperature	Tstg	–55 to +150	°C

Note: Marking is "YA–"
Attention: This device is very sensitive to electro static discharge.
It is recommended to adopt appropriate cautions when handling this transistor.

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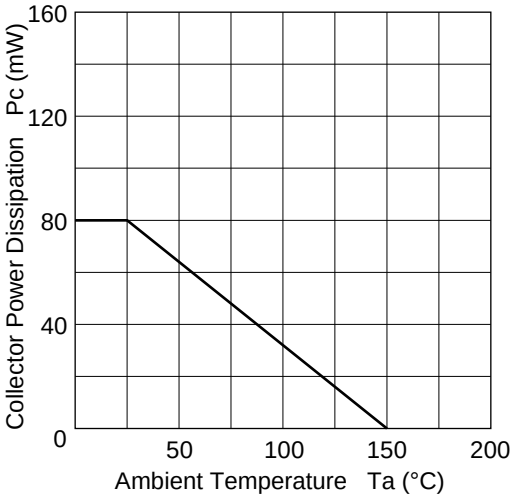
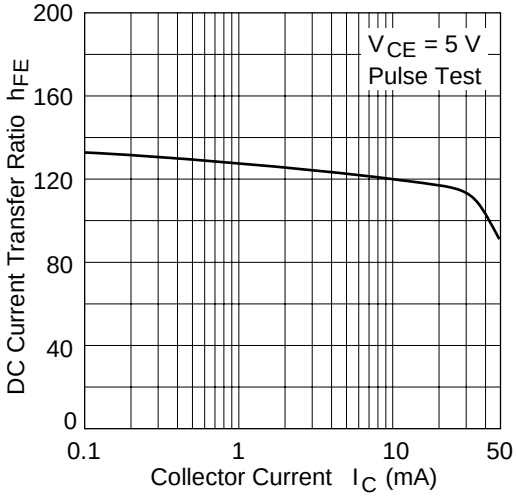
Table 2 Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min.	Typ.	Max.	Unit	Test conditions
Collector cutoff current	I_{CBO}	—	—	10	µA	V_{CB} = 15 V, I_E = 0
	I_{CEO}	—	—	1	mA	V_{CE} = 8 V, R_{BE} = ∞
Emitter cutoff current	I_{EBO}	—	—	10	µA	V_{EB} = 1.5 V, I_C = 0
DC current transfer ratio	h_{FE}	50	120	250		V_{CE} = 5 V, I_C = 10 mA
Output capacitance	Cob	—	0.45	0.8	pF	V_{CB} = 5 V, I_E = 0, f = 1 MHz
Gain bandwidth product	f_T	7	10	—	GHz	V_{CE} = 5 V, I_C = 10 mA
Power gain	PG	12	16.5	—	dB	V_{CE} = 5 V, I_C = 10 mA, f = 900 MHz
Noise figure	NF	—	1.5	2.5	dB	V_{CE} = 5 V, I_C = 5 mA, f = 900 MHz

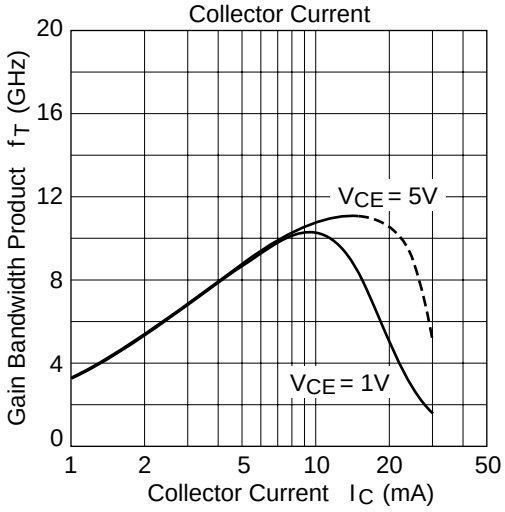
Maximum Collector Power Dissipation Curve



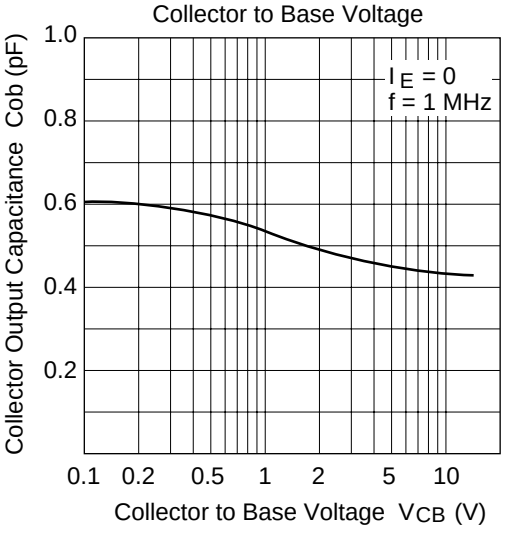
DC Current Transfer Ratio vs. Collector Current



Gain Bandwidth Product vs. Collector Current



Collector Output Capacitance vs. Collector to Base Voltage



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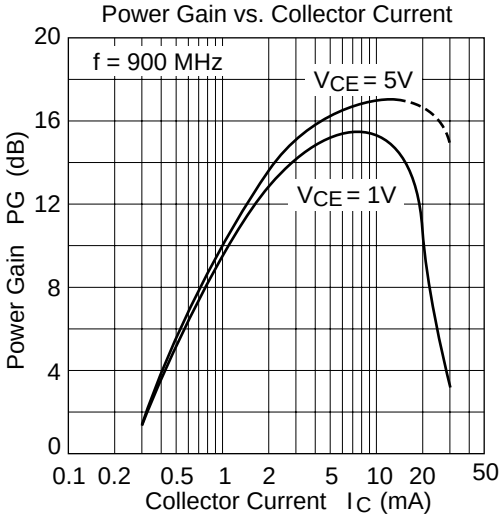
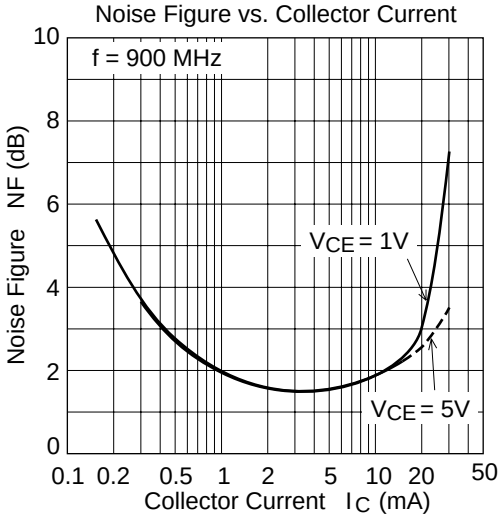
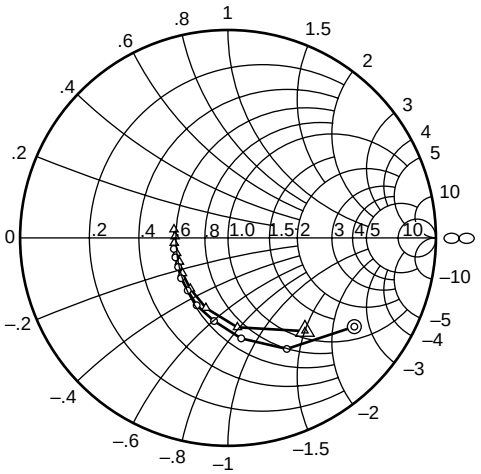
Power Gain vs. Collector Current



Noise Figure vs. Collector Current

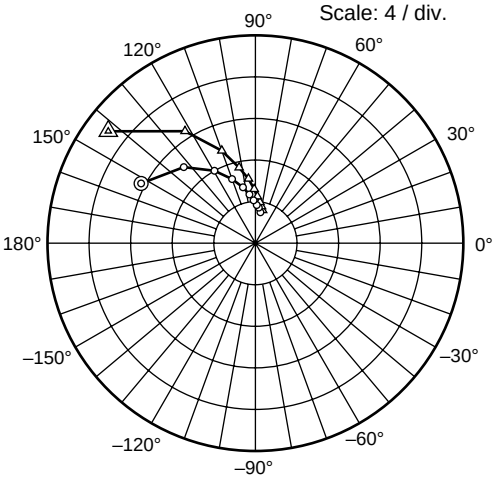


S11 Parameter vs. Frequency



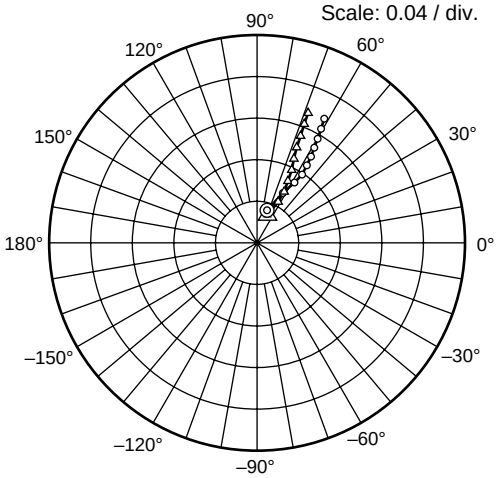
Condition: V_{CE}= 5 V , Zo = 50 Ω
200 to 2000 MHz (200 MHz step)
(I_C = 5 mA)
(I_C = 10 mA)

S21 Parameter vs. Frequency



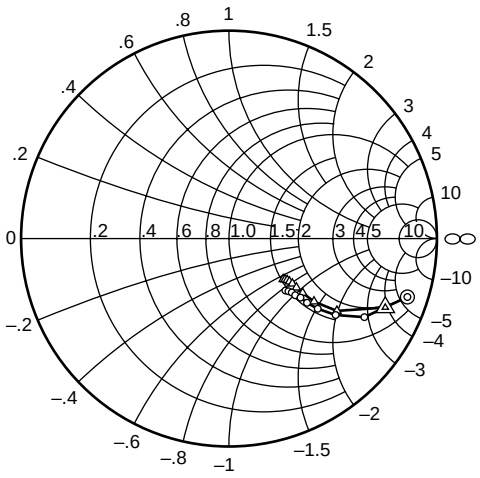
Condition: V_{CE}= 5 V , Zo = 50 Ω
200 to 2000 MHz (200 MHz step)
(I_C = 5 mA)
(I_C = 10 mA)

S12 Parameter vs. Frequency



Condition: V_{CE}= 5 V , Zo = 50 Ω
200 to 2000 MHz (200 MHz step)
(I_C = 5 mA)
(I_C = 10 mA)

S22 Parameter vs. Frequency



Condition: V_{CE}= 5 V , Zo = 50 Ω
200 to 2000 MHz (200 MHz step)
(I_C = 5 mA)
(I_C = 10 mA)

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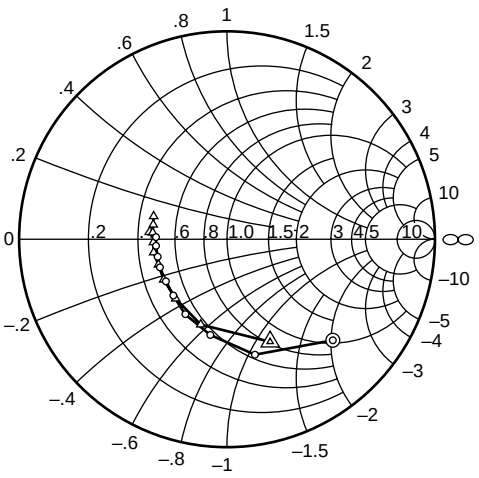
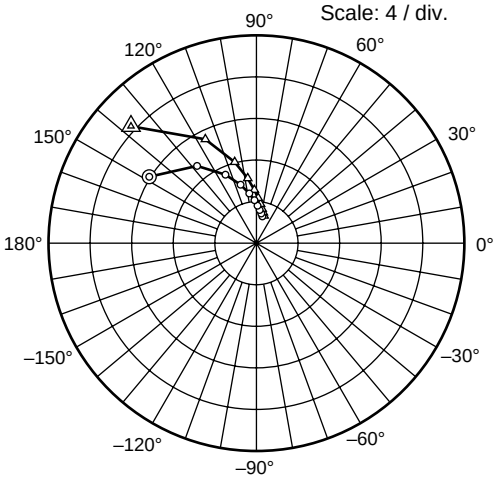
S11 Parameter vs. Frequency



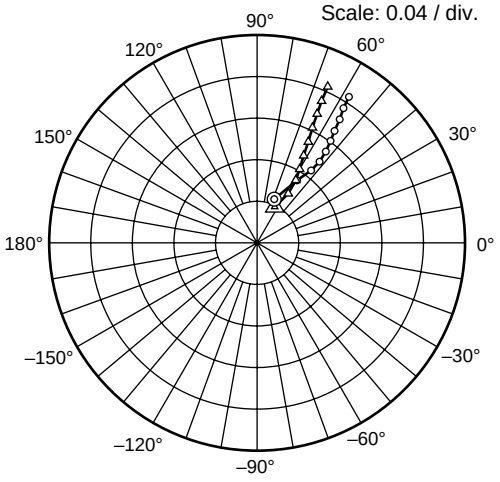
Condition: V_{CE} = 1 V , Zo = 50 Ω
200 to 2000 MHz (200 MHz step)
(I_C = 5 mA)
(I_C = 10 mA)

S21 Parameter vs. Frequency



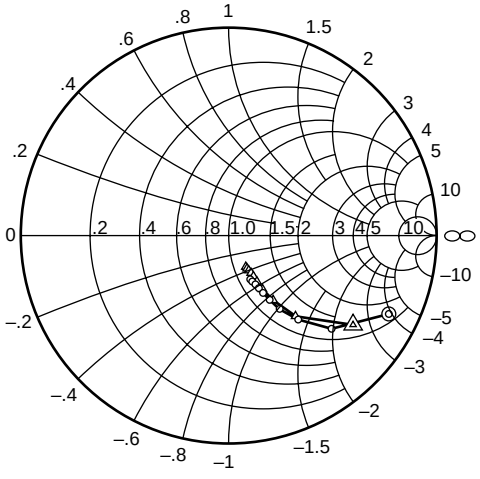
Condition: V_{CE} = 1 V , Zo = 50 Ω
200 to 2000 MHz (200 MHz step)
(I_C = 5 mA)
(I_C = 10 mA)

S12 Parameter vs. Frequency



Condition: V_{CE} = 1 V , Zo = 50 Ω
200 to 2000 MHz (200 MHz step)
(I_C = 5 mA)
(I_C = 10 mA)

S22 Parameter vs. Frequency



Condition: V_{CE} = 1 V , Zo = 50 Ω
200 to 2000 MHz (200 MHz step)
(I_C = 5 mA)
(I_C = 10 mA)

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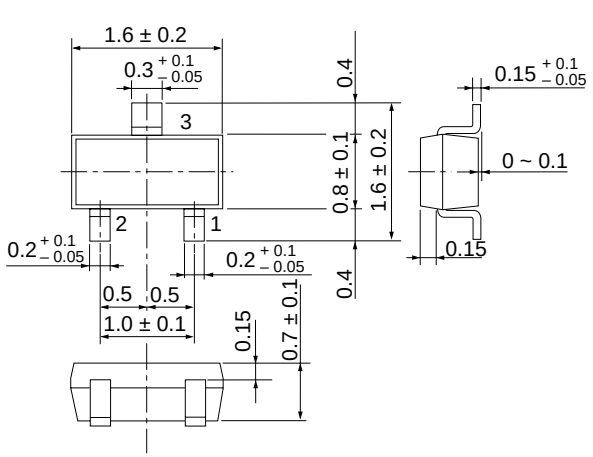
Package Dimensions

Unit : mm



1. Emitter
2. Base
3. Collector

Hitachi Code	SMPAK
EIAJ	—
JEDEC	—